NL17SZ08E

Single 2-Input AND Gate

The NL17SZ08E is a single 2-input AND Gate in three tiny footprint packages. The device performs much as LCX multi-gate products in speed and drive. They should be used wherever the need for higher speed and drive are needed.

Features

- Tiny SOT-353 Package
- 2.7 ns T_{PD} at 5.0 V (typ)
- Source/Sink 24 mA at 3.0 V
- Overvoltage Tolerant Inputs
- Chip Complexity: FETs = 20
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

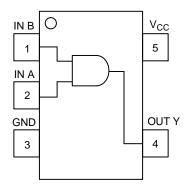


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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L2 = Specific Device Marking

= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	IN B
2	IN A
3	GND
4	OUT Y
5	V _{CC}

FUNCTION TABLE

Inp	Output Y = AB	
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NL17SZ08E

MAXIMUM RATINGS

Symbol	Parameter		Value	Units
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
V _{OUT}	DC Output Voltage	Active Mode, High or LOW State Power Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current		-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA
I _{OUT}	DC Output Sink Current		±50	mA
I _{CC}	DC Supply Current per Supply Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance	(Note 1)	350	°C/W
P _D	Power Dissipation in Still Air at 85°C		186	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
ESD	ESD Classification	Human Body Model (Note 2) Charged Device Model (Note 3)	4000 1000	V
I _{LATCHUP}	Latchup Performance Above V _{CC} and Below GND at 1	25°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
 Tested to EIA/JESD22-A114-A, rated to EIA/JESD22-A114-B.
- Tested to JESD22-C101-A.
 Tested to EIA/JESD78.

NL17SZ08E

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Units
V _{CC}	DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	Active Mode, LOW State Power–Down Mode ($V_{CC} = 0 \text{ V}$)	0 0	V _{CC} 5.5	V
T _A	Operating Temperature Range		- 55	+125	°C
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 2.5 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		С	-55°C ≤ T _A ≤ 125°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V _{IH}	High-Level Input Voltage		1.65 to 1.95 2.3 to 5.5	0.75 V _{CC} 0.7 V _{CC}			0.75 V _{CC} 0.7 V _{CC}		V
V_{IL}	Low-Level Input Voltage		1.65 to 1.95 2.3 to 5.5			0.25 V _{CC} 0.3 V _{CC}		0.25 V _{CC} 0.3 V _{CC}	V
V _{OH}	High-Level Output Voltage	$I_{OH} = -100 \mu A$	1.65 to 5.5	V _{CC} - 0.1	V_{CC}		V _{CC} - 0.1		V
	$V_{IN} = V_{II}$ or V_{IH}	$I_{OH} = -4 \text{ mA}$	1.65	1.29	1.52		1.29		
		$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.1		1.9		
		$I_{OH} = -12 \text{ mA}$	2.7	2.2	2.4		2.2		
		$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.7		2.4		
		$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.5		2.3		
		$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.0		3.8		
V _{OL}	Low-Level Output Voltage	I _{OL} = 100 μA	1.65 to 5.5			0.1		0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{OH}$	$I_{OL} = 4 \text{ mA}$	1.65		0.08	0.24		0.24	
		$I_{OL} = 8 \text{ mA}$	2.3		0.20	0.3		0.3	
		$I_{OL} = 12 \text{ mA}$	2.7		0.22	0.4		0.4	
		$I_{OL} = 16 \text{ mA}$	3.0		0.28	0.4		0.4	
		$I_{OL} = 24 \text{ mA}$	3.0		0.38	0.55		0.55	
		$I_{OL} = 32 \text{ mA}$	4.5		0.42	0.55		0.55	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5			±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5			1		10	μА
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0			1		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS $t_R = t_F = 3.0 \text{ ns}$

			V _{CC}		T _A = 25°C	;	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
t _{PLH}	Propagation Delay	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	1.65		6.3	12		12.7	ns
t _{PHL}	(Figure 3 and 4)	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	1.8		6.2	10		10.5	
		$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	2.5 ± 0.2		3.4	7.0		7.5	
		$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	3.3 ± 0.3		2.6	4.7		5.0	
		$R_L = 500 \ \Omega, C_L = 50 \ pF$			3.3	5.2		5.5	
		$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$	5.0 ± 0.5		2.2	4.1		4.4	
		$R_L = 500 \Omega, C_L = 50 pF$			2.7	4.5		4.8	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	>4.0	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF
	(Note 5)	10 MHz, V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	30	

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

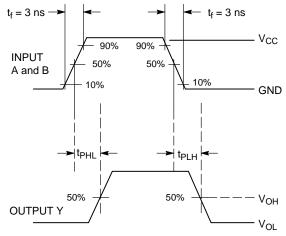
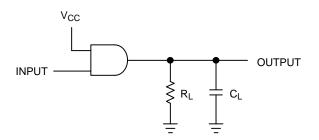


Figure 3. Switching Waveform



A 1–MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Tape and Reel Size [†]
NL17SZ08EDFT2G	SC-88A/SC-70-5/SOT-353 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE L**

DATE 17 JAN 2013



- TIES:
 DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 419A-01 OBSOLETE. NEW STANDARD 3.
- 419A-02.
 DIMENSIONS A AND B DO NOT INCLUDE
- MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

-B-S D 5 PL 0.2 (0.008) M B M **SOLDER FOOTPRINT**

+++			
0.40			0.65 0.025
	<u>1.9</u> 0.0748	SCALE 20:1	$\left(\frac{\text{mm}}{\text{inches}}\right)$
OT # F 4	07450	07.45.0	

0.50 0.0197

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE 1	PIN 1. SOURCE 1	PIN 1. CATHODE
2. EMITTER	2. EMITTER	2. N/C	2. DRAIN 1/2	2. COMMON ANODE
3. BASE	3. BASE	3. ANODE 2	3. SOURCE 1	3. CATHODE 2
4. COLLECTOR	4. COLLECTOR	4. CATHODE 2	4. GATE 1	4. CATHODE 3
4. COLLECTOR	4. COLLECTOR	4. CATHODE 2	4. GATE 1	4. CATHODE 3
5. COLLECTOR	5. CATHODE	5. CATHODE 1	5. GATE 2	5. CATHODE 4

J. GOLLLOTON	3. CATTODE	J. CATHODE I	J. GAIL 2	J. CATTODE 4
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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